



### FEATURES

- 5.7 kV rms, signal isolated RS-485/RS-422 transceiver
- 1500 V peak/dc working voltage to DIN V VDE V 0884-11
- Low radiated emissions: passes EN55032 Class B with margin on a 2-layer PCB
- Receiver cable inversion smart feature
  - Correction for reversed cable connection on A and B bus pins while maintaining full receiver fail-safe
- ESD protection on the RS-485 A, B, Y, and Z bus pins
  - $\geq \pm 12$  kV IEC61000-4-2 contact discharge
  - $\geq \pm 15$  kV IEC61000-4-2 air discharge
- Low speed 500 kbps data rate for EMI control
- Flexible power supply inputs
  - Primary  $V_{DD1}$  supply of 1.7 V to 5.5 V
  - Isolated  $V_{DD2}$  supply of 3.0 V to 5.5 V
- Profibus<sup>®</sup> Compliant for 5V  $V_{DD2}$
- Wide  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$  operating temperature range
- High common-mode transient immunity:  $>250$  kV/ $\mu\text{s}$
- Short-circuit, open-circuit, and floating input receiver fail-safe
- Supports 192 bus nodes (72 k $\Omega$  receiver input impedance)
- Full hot swap support (glitch free power-up and power-down)
- Safety and regulatory approvals (pending)
  - CSA Component Acceptance Notice 5A, DIN V VDE V 0884-11, UL 1577, CQC11-471543-2012, IEC 61010-1
- 16-lead, wide body, SOIC package with  $>8.0$  mm creepage and clearance in standard pinout

### APPLICATIONS

- Solar inverters
- Electrical test and measurement
- Heating, ventilation, and air-conditioning (HVAC) networks
- Industrial field buses
- Building automation

### GENERAL DESCRIPTION

The ADM2763E is a 500 kbps, 5.7 kV rms, signal isolated RS-485 transceiver that passes radiated emissions testing to the EN55032 Class B standard with margin on a 2-layer printed circuit board (PCB). The ADM2763E isolation barrier provides robust system level immunity to IEC61000-4-x system level EMC standards. The device is suitable for applications which require insulation against working voltages of 1060 V rms and 1500V dc for the lifetime of the device. The devices is protected against  $\geq \pm 12$  kV contact and  $\geq \pm 15$  kV air IEC61000-4-2 electrostatic discharge (ESD) events on the RS-485 A, B, Y, and Z pins. The ADM2763E features a receiver cable invert pin to allow quick correction of the reversed cable connection on the

### FUNCTIONAL BLOCK DIAGRAM

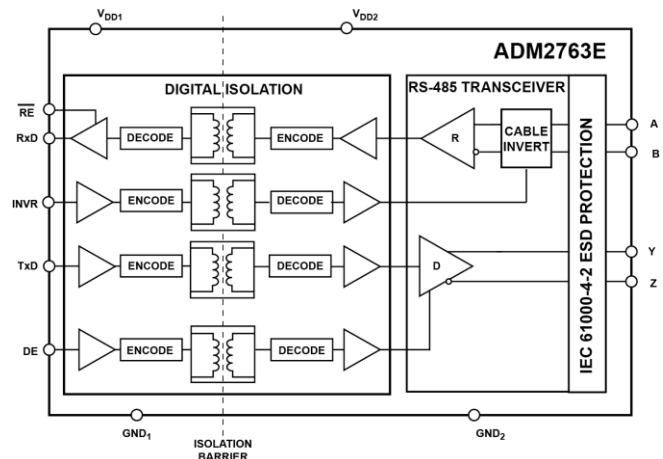


Figure 1.

A and B receiver bus pins while maintaining full receiver fail-safe performance.

The ADM2763E is optimized for low speed over long cable runs and has a maximum data rate of 500 kbps. The high differential output voltage makes this device suitable for Profibus nodes when powered with 5 V on the  $V_{DD2}$  supply. The  $V_{DD1}$  primary supply and  $V_{DD2}$  isolated supply both support a wide range of voltages (1.7 V to 5.5 V and 3 V to 5.5V, respectively). This full duplex device is available in the industry standard 16-lead, wide body, standard SOIC package with  $>8.0$  mm creepage and clearance.

### Rev. PrA

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## SPECIFICATIONS

All voltages are relative to the respective ground,  $1.7\text{ V} \leq V_{DD1} \leq 5.5\text{ V}$ ,  $3.0\text{ V} \leq V_{DD2} \leq 5.5\text{ V}$ ,  $T_A = T_{MIN} (-40^\circ\text{C})$  to  $T_{MAX} (+125^\circ\text{C})$ . All minimum and maximum specifications apply over the entire recommended operation range, unless otherwise noted. All typical specifications are at  $T_A = 25^\circ\text{C}$ ,  $V_{DD1} = V_{DD2} = 3.3\text{ V}$ , unless otherwise noted. {now filled out}

Table 1.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
PRIMARY SIDE SUPPLY CURRENT	$I_{DD1(Q)}$		0.6	1	mA	DE = 0 V
	$I_{DD1}$		2	8	mA	DE = $V_{DD1}$
ISOLATED SIDE SUPPLY CURRENT	$I_{DD2(Q)}$		5	8	mA	$V_{DD2} \leq 3.6\text{ V}$ , (DE = 0V)
			5	8	mA	$V_{DD2} \geq 4.5\text{ V}$ , (DE = 0V)
	$I_{DD2}$		6	9	mA	$V_{DD2} \leq 3.6\text{ V}$ , (DE = $V_{DD1}$ )
			6	9	mA	$V_{DD2} \geq 4.5\text{ V}$ , (DE = $V_{DD1}$ )
ISOLATED SIDE DYNAMIC SUPPLY CURRENT	$I_{DD2(DYN)}$		58	78	mA	$V_{DD2} \leq 3.6\text{ V}$ , $R_L = 54\ \Omega$ , (DE = $V_{DD1}$ , $\overline{RE} = 0\text{ V}$ ), data rate = 500 kbps
			100	145	mA	$V_{DD2} \geq 4.5\text{ V}$ , $R_L = 54\ \Omega$ , (DE = $V_{DD1}$ , $\overline{RE} = 0\text{ V}$ ), data rate = 500 kbps
DRIVER DIFFERENTIAL OUTPUTS						
Differential Output Voltage, Loaded	$ V_{OD2} $	2.0	2.5	$V_{DD2}$	V	$V_{DD2} \geq 3.0\text{ V}$ , $R_L = 100\ \Omega$ , see Figure 22
Over Common-Mode Range	$ V_{OD3} $	1.5	2.1	$V_{DD2}$	V	$V_{DD2} \geq 3.0\text{ V}$ , $R_L = 54\ \Omega$ , see Figure 22
		2.1	3.3	$V_{DD2}$	V	$V_{DD2} \geq 4.5\text{ V}$ , $R_L = 54\ \Omega$ , see Figure 22
		1.5	2.1	$V_{DD2}$	V	$V_{DD2} \geq +3.0\text{ V}$ , $-7\text{ V} \leq V_{CM} \leq +12\text{ V}$ , see Figure 23
		2.1	3.3	$V_{DD2}$	V	$V_{DD2} \geq +4.5\text{ V}$ , $-7\text{ V} \leq V_{CM} \leq +12\text{ V}$ , see Figure 23
$\Delta V_{OD2} $ for Complementary Output States	$\Delta V_{OD2} $			0.2	V	$R_L = 54\ \Omega$ or $100\ \Omega$ , see Figure 22
Common-Mode Output Voltage	$V_{OC}$		1.5	3.0	V	$R_L = 54\ \Omega$ or $100\ \Omega$ , see Figure 22
$\Delta V_{OC} $ for Complementary Output States	$\Delta V_{OC} $			0.2	V	$R_L = 54\ \Omega$ or $100\ \Omega$ , see Figure 22
Short-Circuit Output Current	$I_{OS}$	-250		+250	mA	$-7\text{ V} < \text{output voltage } (V_{OUT}) < +12\text{ V}$
Output Leakage Current (Y, Z) <sup>1</sup>	$I_O$		1	50	$\mu\text{A}$	DE = $\overline{RE} = 0\text{ V}$ , $V_{DD2} = 0\text{ V}$ or $5.5\text{ V}$ , input voltage ( $V_{IN}$ ) = $12\text{ V}$
		-50	+10		$\mu\text{A}$	DE = $\overline{RE} = 0\text{ V}$ , $V_{DD2} = 0\text{ V}$ or $+5.5\text{ V}$ , $V_{IN} = -7\text{ V}$
Pin Capacitance (Y, Z)	$C_{IN}$		28		pF	$V_{IN} = 0.4\sin(10\pi t \times 10^6)$
RECEIVER DIFFERENTIAL INPUTS						
Differential Input Threshold Voltage, Noninverted	$V_{TH}$	-200	-125	-30	mV	$-7\text{ V} < V_{CM} < +12\text{ V}$ , INVR = 0 V
Differential Input Threshold Voltage, Inverted		30	125	200	mV	$-7\text{ V} < V_{CM} < +12\text{ V}$ , INVR = $V_{DD1}$
Input Voltage Hysteresis	$V_{HYS}$		25		mV	$-7\text{ V} < V_{CM} < +12\text{ V}$
Input Current (A, B)	$I_I$			167	$\mu\text{A}$	DE = 0 V, $V_{DD2} = \text{powered/unpowered}$ , $V_{IN} = 12\text{ V}$
		-133			$\mu\text{A}$	DE = 0 V, $V_{DD2} = \text{powered/unpowered}$ , $V_{IN} = -7\text{ V}$
Pin Capacitance (A, B)	$C_{IN}$		4		pF	$V_{IN} = 0.4\sin(10\pi t \times 10^6)$
DIGITAL LOGIC INPUTS						
Input Low Voltage	$V_{IL}$			$0.3 \times V_{DD1}$	V	DE, $\overline{RE}$ , TxD, INVR
Input High Voltage	$V_{IH}$	$0.7 \times V_{DD1}$			V	DE, $\overline{RE}$ , TxD, INVR
Input Current	$I_I$	-2	+0.01	+2	$\mu\text{A}$	DE, $\overline{RE}$ , TxD, $V_{IN} = 0\text{ V}$ or $V_{DD1}$
		-2	+10	+30	$\mu\text{A}$	INVR, $V_{IN} = 0\text{ V}$ or $V_{DD1}$

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
RXD DIGITAL OUTPUT						
Output Voltage Low	$V_{OL}$			0.4	V	$V_{DD1} = +3.6\text{ V}$ , output current ( $I_{OUT}$ ) = +2.0 mA, $V_A - V_B \leq -0.2\text{ V}$
				0.4	V	$V_{DD1} = +2.7\text{ V}$ , $I_{OUT} = +1.0\text{ mA}$ , $V_A - V_B \leq -0.2\text{ V}$
				0.2	V	$V_{DD1} = +1.95\text{ V}$ , $I_{OUT} = +500\text{ }\mu\text{A}$ , $V_A - V_B \leq -0.2\text{ V}$
Output Voltage High	$V_{OH}$	2.4			V	$V_{DD1} = +3.0\text{ V}$ , $I_{OUT} = -2.0\text{ mA}$ , $V_A - V_B \geq -0.03\text{ V}$
		2.0			V	$V_{DD1} = +2.3\text{ V}$ , $I_{OUT} = -1.0\text{ mA}$ , $V_A - V_B \geq -0.03\text{ V}$
		$V_{DD1} - 0.2$			V	$V_{DD1} = +1.7\text{ V}$ , $I_{OUT} = -500\text{ }\mu\text{A}$ , $V_A - V_B \geq -0.03\text{ V}$
Short-Circuit Current				100	mA	$V_{OUT} = GND_1$ or $V_{DD1}$ , $\overline{RE} = 0\text{ V}$
Three-State Output Leakage Current	$I_{OZR}$	-1	+0.01	+1	$\mu\text{A}$	$\overline{RE} = V_{DD1}$ , $RxD = 0\text{ V}$ or $V_{DD1}$
COMMON-MODE TRANSIENT IMMUNITY (CMTI) <sup>1</sup>		250			kV/ $\mu\text{s}$	$V_{CM} \geq \pm 1\text{ kV}$ , transient magnitude measured between 20% and 80% of $V_{CM}$ , see Figure 33

<sup>1</sup>The CMTI is the maximum common-mode voltage slew rate that can be sustained while maintaining specification compliant operation.  $V_{CM}$  is the common-mode potential difference between the logic and bus sides. The transient magnitude is the range over which the common mode is slewed. The common-mode voltage slew rates apply to rising and falling common-mode voltage edges.

## TIMING SPECIFICATIONS

$V_{DD1} = 1.7\text{ V}$  to  $5.5\text{ V}$ ,  $V_{DD2} = 3.0\text{ V}$  to  $5.5\text{ V}$ ,  $T_A = T_{MIN} (-40^\circ\text{C})$  to  $T_{MAX} (+125^\circ\text{C})$ , unless otherwise noted. All typical specifications are at  $T_A = 25^\circ\text{C}$ ,  $V_{DD1} = V_{DD2} = 3.3\text{ V}$ , unless otherwise noted.

Table 2.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
DRIVER						
Maximum Data Rate		500			kbps	
Propagation Delay	$t_{DPLH}$ , $t_{DPLH}$		230	400	ns	$R_L = 54\text{ }\Omega$ , $C_L = 100\text{ pF}$ , see Figure 24 and Figure 28
Output Skew	$t_{SKEW}$		3	100	ns	$R_L = 54\text{ }\Omega$ , $C_L = 100\text{ pF}$ , see Figure 24 and Figure 28
Rise Time and Fall Time	$t_{DR}$ , $t_{DF}$	200	400	800	ns	$R_L = 54\text{ }\Omega$ , $C_L = 100\text{ pF}$ , see Figure 24 and Figure 28
Enable Time	$t_{ZL}$ , $t_{ZH}$		150	1000	ns	$R_L = 110\text{ }\Omega$ , $C_L = 50\text{ pF}$ , see Figure 25 and Figure 30
Disable Time	$t_{LZ}$ , $t_{HZ}$		1700	2200	ns	$R_L = 110\text{ }\Omega$ , $C_L = 50\text{ pF}$ , see Figure 25 and Figure 30
RECEIVER						
Propagation Delay	$t_{RPLH}$ , $t_{RPHL}$		30	200	ns	$C_L = 15\text{ pF}$ , see Figure 26 and Figure 29
Output Skew	$t_{SKEW}$		2.5	50	ns	$C_L = 15\text{ pF}$ , see Figure 26 and Figure 29
Enable Time	$t_{ZL}$ , $t_{ZH}$		3	50	ns	$R_L = 1\text{ k}\Omega$ , $C_L = 15\text{ pF}$ , see Figure 27 and Figure 31
Disable Time	$t_{LZ}$ , $t_{HZ}$		8	50	ns	$R_L = 1\text{ k}\Omega$ , $C_L = 15\text{ pF}$ , see Figure 27 and Figure 31
RECEIVER CABLE INVERT (INVR)						
Propagation Delay	$t_{INVRPHL}$ , $t_{INVRPLH}$		20	40	ns	$V_{ID} \geq -200\text{ mV}$ or $V_{ID} \leq +200\text{ mV}$ , see Figure 32

## PACKAGE CHARACTERISTICS

Table 3.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Resistance (Input to Output) <sup>1</sup>	$R_{IO}$		$10^{13}$		$\Omega$	
Capacitance (Input to Output) <sup>1</sup>	$C_{IO}$		2.2		pF	Test frequency = 1 MHz
Input Capacitance <sup>2</sup>	$C_I$		3.0		pF	Input Capacitance

<sup>1</sup> The device is considered a 2-terminal device. Short together Pin 1 through Pin 8 and short together Pin 9 through Pin 16 to set the device up as a 2-terminal device during testing.

<sup>2</sup> Input capacitance is from any input data pin to ground.

**INSULATION AND SAFETY RELATED SPECIFICATIONS**

For additional information, see [www.analog.com/icouplersafety](http://www.analog.com/icouplersafety).

**Table 4. Critical Safety Related Dimensions and Material Properties**

Parameter	Symbol	Value	Unit	Conditions
Rated Dielectric Insulation Voltage		5700	V rms	1-minute duration
Minimum External Air Gap (Clearance)	L(I01)	8.3	mm	Measured from input terminals to output terminals, shortest distance through air
Minimum External Tracking (Creepage)	L(I02)	8.3	mm	Measured from input terminals to output terminals, shortest distance along body
Minimum Clearance in the Plane of the Printed Circuit Board (PCB Clearance)	L (PCB)	8.1	mm	Measured from input terminals to output terminals, shortest distance through air, line of sight, in the PCB mounting plane
Minimum Internal Gap (Internal Clearance)		43	µm min	Insulation distance through insulation
Tracking Resistance (Comparative Tracking Index) Material Group	CTI	>600 I	V	DIN IEC 112/VDE 0303 Part 1 Material Group (DIN VDE 0110: 1989-01, Table 1)

**REGULATORY INFORMATION**

**Table 5. ADM2763E Approvals**

UL (Pending)	CSA (Pending)	VDE (Pending)	CQC (Pending)
Recognized Under UL 1577 Component Recognition Protection <sup>1</sup>	Approved under CSA Component Acceptance Notice 5A	To be certified under DIN V VDE 0884-11 <sup>2</sup>	Certified under CQC11-471543-2012
Single Protection, 5700 V rms	CSA 60950-1-07+A1+A2 and IEC 60950-1, second edition, +A1+A2: Basic insulation at 800 V rms (1131 V peak) Reinforced insulation at 400 V rms (565 V peak) IEC 62368-1, first edition Basic insulation at 800 V rms (1131 V peak) Reinforced insulation at 400 V rms (565 V peak) IEC 60601-1 Edition 3.1:  1 means of patient protection (1 MOPP), 400 V rms (565 V peak) 2 MOPP, 250 V rms (353 V peak) 1 or 2 means of operator protection (1 MOPP or 2 MOPP), 400 V rms (565 V peak) CSA 61010-1-12 and IEC 61010-1 third edition: Basic insulation at 300 V rms mains, 800 V rms (1131 V peak) from secondary circuit Reinforced insulation at 300 V rms mains, 400 V rms (565 V peak) from secondary circuit	Basic insulation:  Working voltage ( $V_{IOWM}$ ) = 1173 V rms Repetitive maximum voltage ( $V_{IORM}$ ) = 1672 V peak <sup>3</sup>  Surge isolation voltage ( $V_{IOSM}$ ) = 10 kV peak Highest allowable overvoltage ( $V_{IOTM}$ ) = 8000 V peak Reinforced insulation: Working voltage ( $V_{IOWM}$ ) = 830 V rms <sup>3</sup>  Repetitive maximum voltage ( $V_{IORM}$ ) = 1173 V peak <sup>3</sup> Surge isolation voltage ( $V_{IOSM}$ ) = 6.25 kV peak Highest allowable overvoltage ( $V_{IOTM}$ ) = 8000 V peak	GB4943.1-2011:  Basic insulation at 800 V rms (1131 V peak) Reinforced insulation at 400 V rms (565 V peak)
File (pending)	File (pending)	File (pending)	File (pending)

<sup>1</sup> In accordance with UL 1577, each ADM2763E is proof tested by applying an insulation test voltage ≥ 6840 V rms for 1 sec.

<sup>2</sup> In accordance with DIN V VDE 0884-11, each ADM2763E is proof tested by applying an insulation test voltage ≥ 3135 for 1 sec (partial discharge detection limit = 5 pC).

<sup>3</sup> Lifetime limited by creepage across device package

**ADM2763E DIN V VDE 0884-11 (VDE 0884-11) INSULATION CHARACTERISTICS (PENDING)**

This isolator is suitable for reinforced electrical isolation only within the safety limit data. Maintenance of the safety data must be ensured by means of protective circuits.

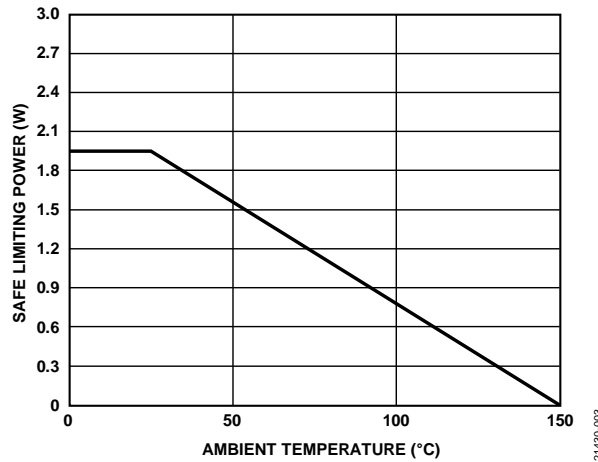


Figure 2. Thermal Derating Curve for 16-Lead, Standard, Wide Body SOIC, Dependence of Safety Limiting Values with Ambient Temperature per DIN V VDE V 0884-10

Table 6.

Description	Conditions	Symbol	Characteristic	Unit
<b>CLASSIFICATIONS</b> Installation Classification per DIN VDE 0110 for Rated Mains Voltage ≤600 V rms ≤1000 V rms ≤1000 V rms Climatic Classification Pollution Degree	Reinforced Insulation Reinforced Insulation Basic Insulation DIN VDE 0110, see Table 1		I to IV I to III I to IV 40/105/21 2	
<b>VOLTAGE</b> Maximum Working Insulation Voltage Maximum Repetitive Peak Insulation Voltage Input to Output Test Voltage Method b1 Method a After Environmental Tests, Subgroup 1 After Input and/or Safety Test, Subgroup 2/Subgroup 3 Highest Allowable Overvoltage Surge Isolation Voltage, Basic Surge Isolation Voltage, Reinforced	$V_{IORM} \times 1.875 = V_{PR}$ , 100% production tested, $t_m = 1$ sec, partial discharge < 5 pC $V_{IORM} \times 1.5 = V_{pd}(m)$ , $t_{ni} = 60$ sec, $t_m = 10$ sec, partial discharge < 5 pC $V_{IORM} \times 1.2 = V_{pd}(m)$ , $t_{ni} = 60$ sec, $t_m = 10$ sec, partial discharge < 5 pC Transient overvoltage, $t_{TR} = 10$ sec $V_{peak} = 10$ kV, 1.2 $\mu$ s rise time, 50 $\mu$ s, 50% fall time $V_{peak} = 10$ kV, 1.2 $\mu$ s rise time, 50 $\mu$ s, 50% fall time	$V_{IOWM}$ $V_{IORM}$ $V_{PR}$   $V_{IOTM}$ $V_{IOSM}$ $V_{IOSM}$	1060 1500 3135 2508 2006 8000 10,000 6250	V rms V peak V peak V peak V peak V peak V peak V peak
<b>SAFETY-LIMITING VALUES</b> Case Temperature Total Power Dissipation at 25°C Insulation Resistance at $T_s$	Maximum value allowed in the event of a failure  $V_{IO} = 500$ V	$T_s$ $P_s$ $R_s$	150 1.95 >10 <sup>9</sup>	°C W $\Omega$

## ABSOLUTE MAXIMUM RATINGS

T<sub>A</sub> = 25°C, unless otherwise noted. All voltages are relative to the respective ground.

Table 7.

Parameter	Rating
V <sub>DD1</sub> to GND <sub>1</sub>	-0.5 V to +7 V
V <sub>DD2</sub> to GND <sub>2</sub>	-0.5 V to +7 V
Digital Input Voltage (DE, $\overline{RE}$ , TxD and INVR)	-0.3 V to V <sub>DD1</sub> +0.3 V
Digital Output Voltage (RxD)	-0.3 V to V <sub>DD1</sub> +0.3 V
Driver Output/Receiver Input Voltage	-9 V to +14 V
Operating Temperature Range	-40°C to +125°C
Storage Temperature Range	-55°C to +150°C
ESD on the Bus Pins (A, B, Y, and Z to GND <sub>2</sub> )	
IEC 61000-4-2 Contact Discharge	≥ ±12 kV
IEC 61000-4-2 Air Discharge	≥ ±15 kV
IEC 61000-4-2 ESD Across Isolation Barrier (A, B, Y, and Z to GND <sub>1</sub> )	±8 kV
ESD (HBM) (V <sub>DD1</sub> , V <sub>DD2</sub> , RxD, DE, $\overline{RE}$ , TxD and INVR)	±4 kV
Lead Temperature	
Soldering (10 sec)	260°C
Vapor Phase (60 sec)	215°C
Infrared (15 sec)	220°C

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

## THERMAL RESISTANCE

Thermal performance is directly linked to PCB design and operating environment. Careful attention to PCB thermal design is required.

θ<sub>JA</sub> is the natural convection junction to ambient thermal resistance measured in a one cubic foot sealed enclosure.

Table 8. Thermal Resistance

Package Type	θ <sub>JA</sub>	Unit
RW-16 <sup>1</sup>	63.9	°C/W

<sup>1</sup> Thermal impedance simulated values are based on JEDEC 2S2P thermal test board with no bias. See JEDEC JESD-51.

Table 9. Maximum Continuous Working Voltage<sup>1,2</sup>

Parameter	Max	Unit	Reference Standard
AC Voltage			
Bipolar Waveform			
Basic Insulation	1500	V peak	50-year minimum lifetime
Reinforced Insulation	1173	V peak	Lifetime limited by package creepage per IEC60664-1
Unipolar Waveform			
Basic Insulation	2710	V peak	Lifetime limited by package creepage per IEC60664-1
Reinforced Insulation	1355	V peak	Lifetime limited by package creepage per IEC60664-1
DC Voltage			
Basic Insulation	1500	V dc	50-year minimum lifetime
Reinforced Insulation	830	V dc	Lifetime limited by package creepage per IEC60664-1

<sup>1</sup> The maximum continuous working voltage refers to continuous voltage magnitude imposed across the isolation barrier. See the Insulation Lifetime section for more details.

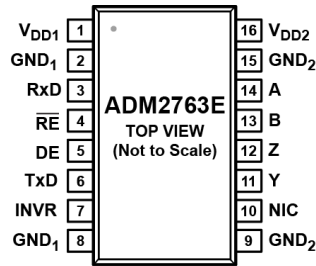
<sup>2</sup> Values are quoted for Material Group I, Pollution Degree II.

## ESD CAUTION



**ESD (electrostatic discharge) sensitive device.** Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

## PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS



## NOTES

1. NIC = NOT INTERNALLY CONNECTED.

Figure 3. ADM2763E Full Duplex Pin Configuration

Table 10. ADM2763E Pin Function Descriptions

Pin No.	Mnemonic	Description
1	V <sub>DD1</sub>	1.7 V to 5.5 V Flexible Primary Side Power Supply. Fit a 0.1 $\mu$ F decoupling capacitor between Pin 1 and Pin 2 to decouple the two supplies. An additional 10 $\mu$ F decoupling capacitor can be fitted between Pin 1 and Pin 2 to improve noise immunity in noisy environments.
2, 8	GND <sub>1</sub>	Ground 1, Logic Side.
3	RxD	Receiver Output Data. When the INVR pin is logic low, this output is high when the differential receiver input voltage (A – B) > –30 mV and low when A – B < –200 mV. When the INVR pin is logic high, this output is high when A – B < 30 mV and low when A – B > 200 mV. When the RE pin is driven high, the receiver disables and this output is tristated.
4	$\overline{\text{RE}}$	Receiver Enable Input. This pin is an active low input. Drive this input low to enable the receiver. Drive this input high to disable the receiver.
5	DE	Driver Output Enable. A high level on this pin enables the driver differential outputs, Y and Z. A low level on this pin places the outputs into a high impedance state.
6	TxD	Transmit Data Input. Data to be transmitted by the driver is applied to this input.
7	INVR	Receiver Cable Invert Input. This pin is an active high input. Drive this pin high to invert the A and B receiver inputs to correct for reversed cable installation. This pin is pulled internally to ground through a high impedance. If the cable invert function is not used, connect this pin to ground.
9, 15	GND <sub>2</sub>	Isolated Ground 2 for the Integrated RS-485 Transceiver, Bus Side.
10	NIC	Not Internally Connected.
11	Y	Driver Noninverting Output.
12	Z	Driver Inverting Output.
13	B	Receiver Inverting Input.
14	A	Receiver Noninverting Input.
16	V <sub>DD2</sub>	3.0 V to 5.5 V Isolated Side Power Supply. Fit a decoupling capacitor of 0.1 $\mu$ F between Pin 16 and Pin 15 to decouple the two supplies. An additional 10 $\mu$ F decoupling capacitor can be fitted between Pin 16 and Pin 15 to improve noise immunity in noisy environments.



### TYPICAL PERFORMANCE CHARACTERISTICS

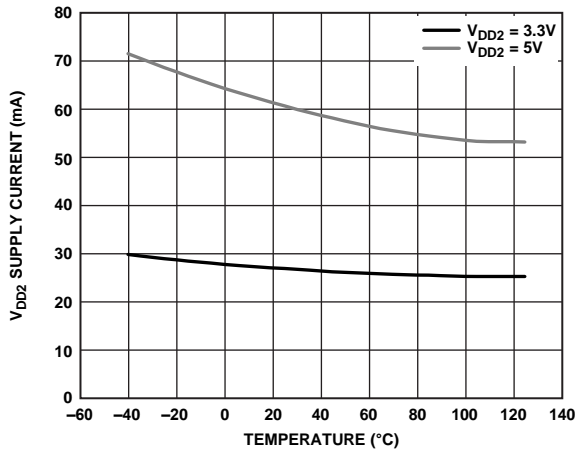


Figure 4. V<sub>DD2</sub> Supply Current vs. Temperature, Data Rate = 500 kbps, No load

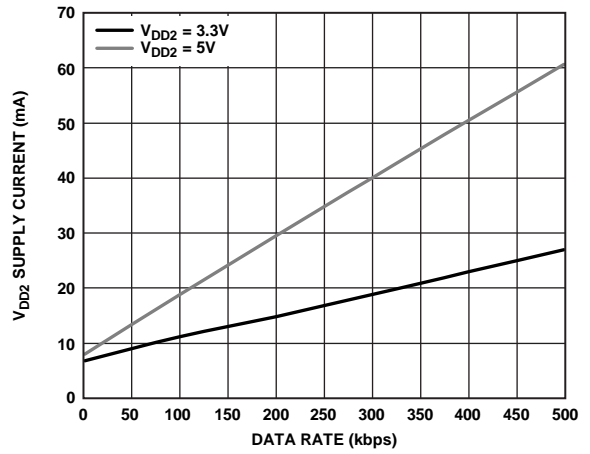


Figure 7. V<sub>DD2</sub> Supply Current vs. Data Rate, T<sub>A</sub> = 25°C, No Load

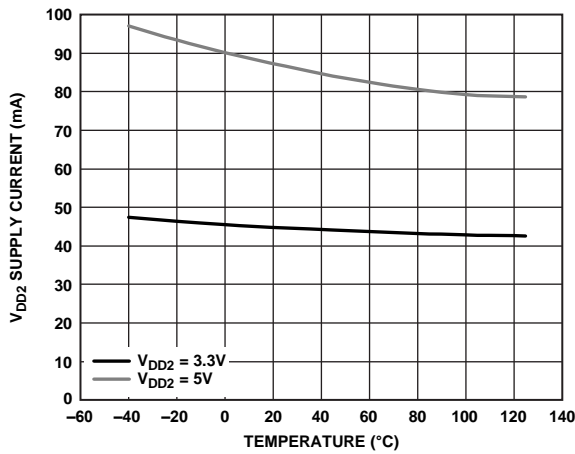


Figure 5. V<sub>DD2</sub> Supply Current vs. Temperature, Data Rate = 500 kbps, R<sub>L</sub> = 120 Ω

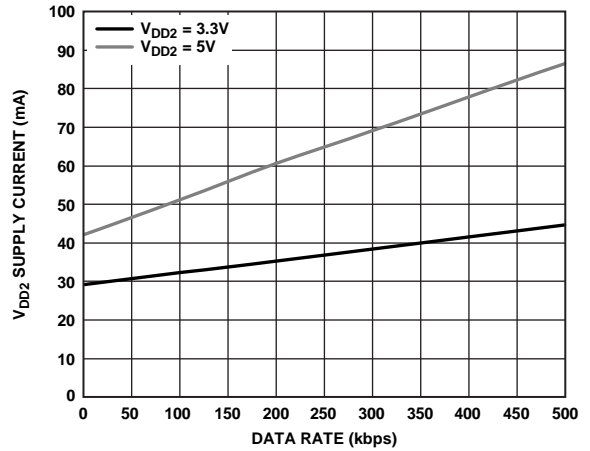


Figure 8. V<sub>DD2</sub> Supply Current vs. Data Rate, T<sub>A</sub> = 25°C, R<sub>L</sub> = 54 Ω

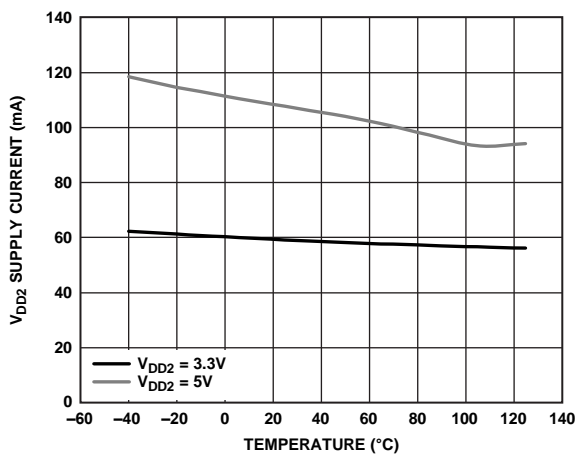


Figure 6. V<sub>DD2</sub> Supply Current vs. Temperature, Data Rate = 500 kbps, R<sub>L</sub> = 54 Ω

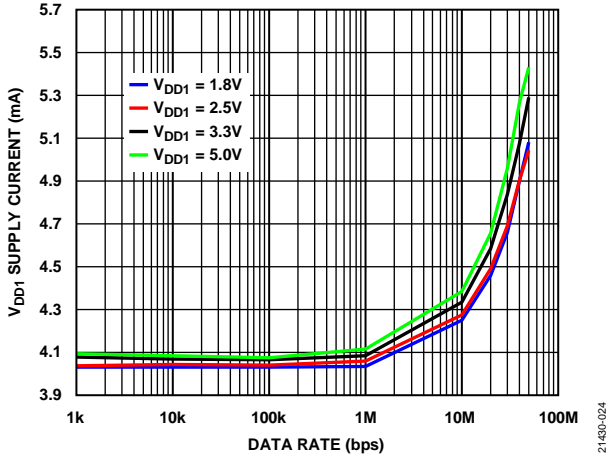


Figure 9.  $V_{DD1}$  Supply Current vs. Data Rate

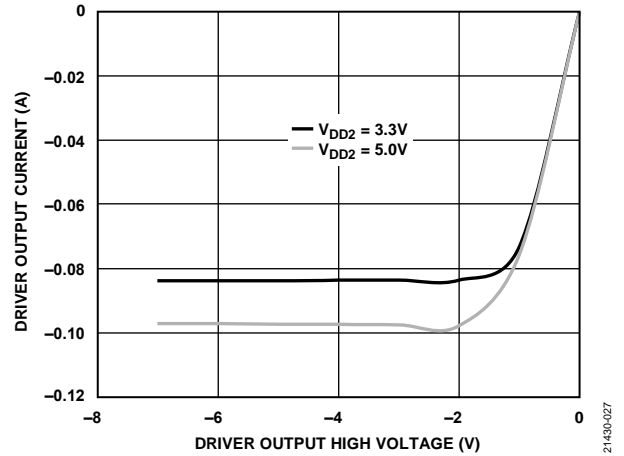


Figure 12. Driver Output Current vs. Driver Output High Voltage

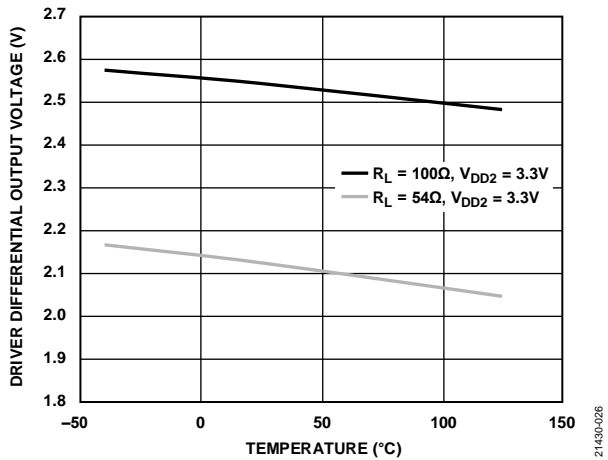


Figure 10. Driver Differential Output Voltage vs. Temperature

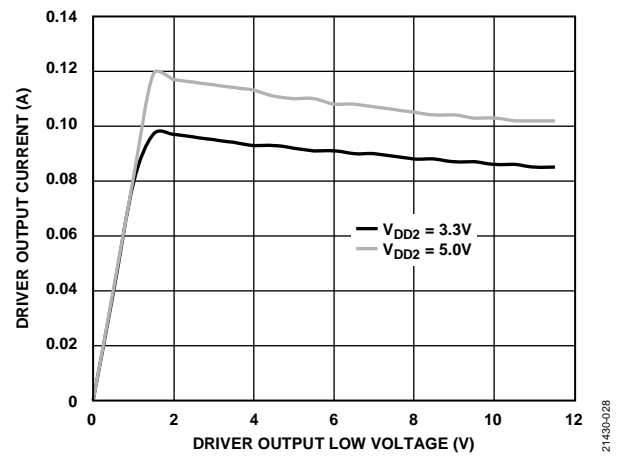


Figure 13. Driver Output Current vs. Driver Output Low Voltage

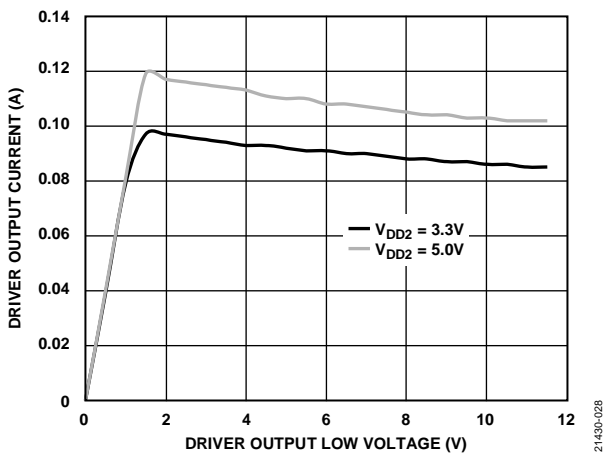


Figure 11. Driver Output Current vs. Driver Differential Output Voltage

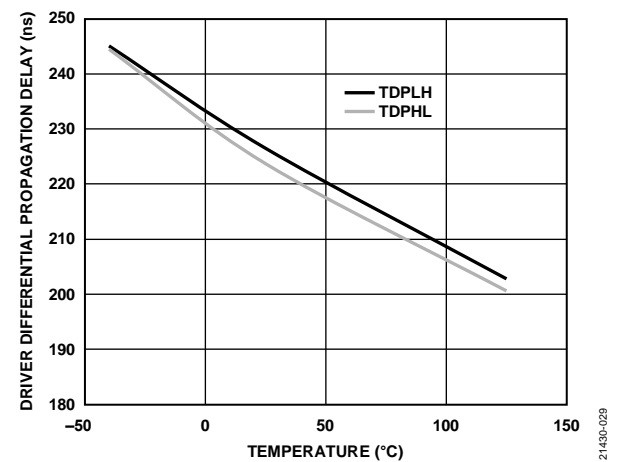


Figure 14. Driver Differential Propagation Delay vs. Temperature

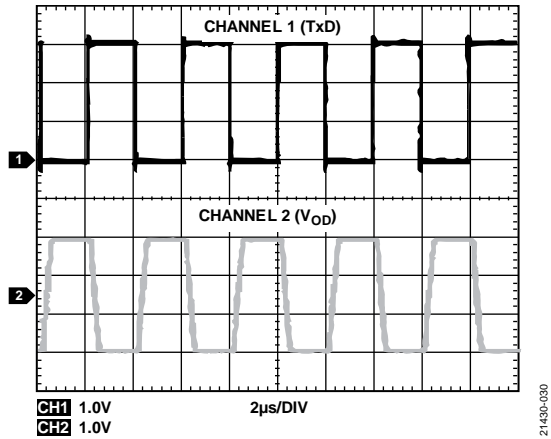


Figure 15. Driver Switching at 500 kbps

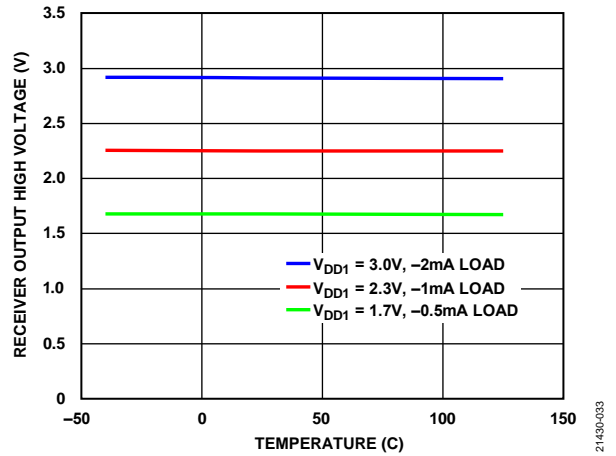


Figure 18. Receiver Output High Voltage vs. Temperature

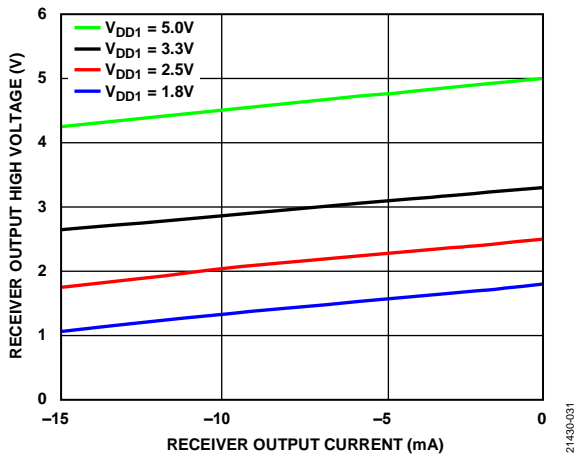


Figure 16. Receiver Output High Voltage vs. Receiver Output Current

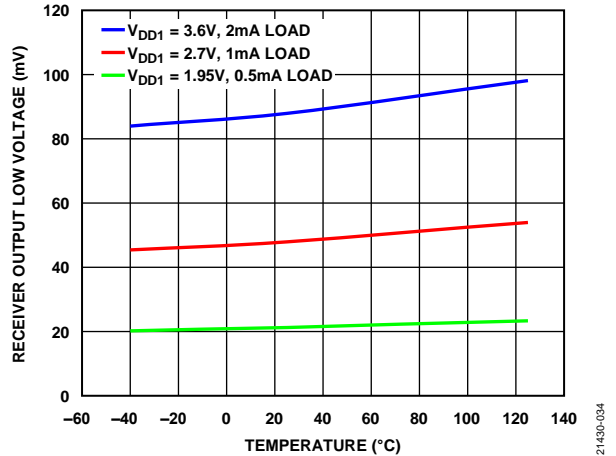


Figure 19. Receiver Output Low Voltage vs. Temperature

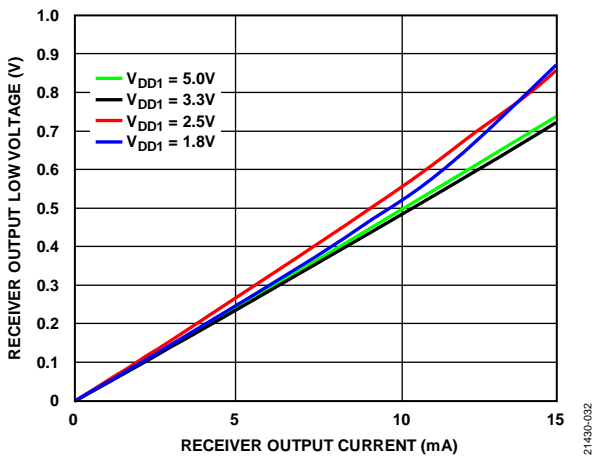


Figure 17. Receiver Output Low Voltage vs. Receiver Output Current

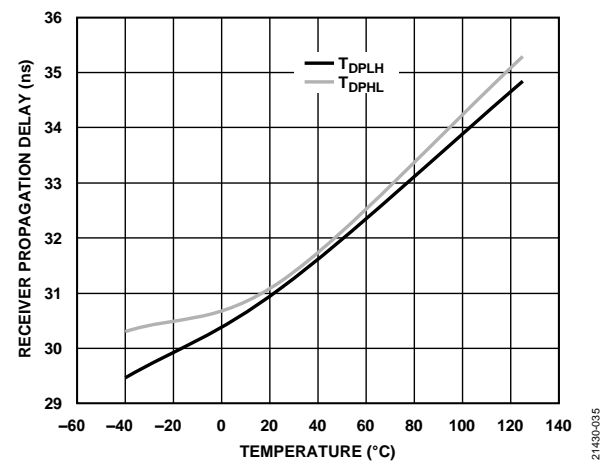


Figure 20. Receiver Propagation Delay vs. Temperature

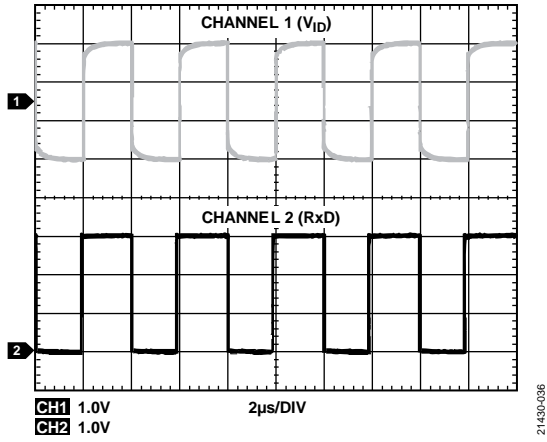


Figure 21. Receiver Switching at 500 kbps

### TEST CIRCUITS AND SWITCHING CHARACTERISTICS

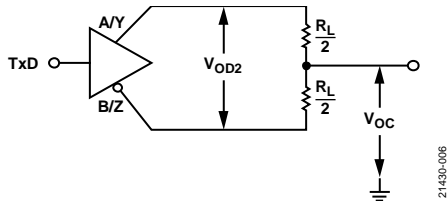


Figure 22. Driver Voltage Measurement  $|V_{OD2}|$

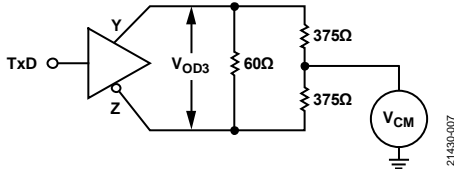


Figure 23. Driver Voltage Measurement over Common-Mode Range  $|V_{OD3}|$

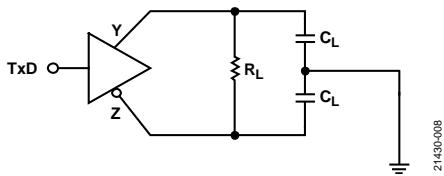


Figure 24. Driver Propagation Delay Measurement

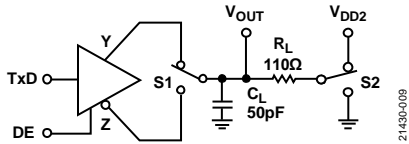


Figure 25. Driver Enable or Disable Time Measurement

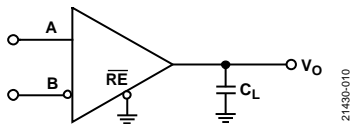


Figure 26. Receiver Propagation Delay Time Measurement

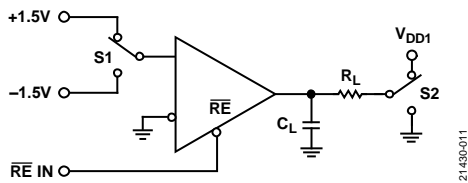


Figure 27. Receiver Enable or Disable Time Measurement

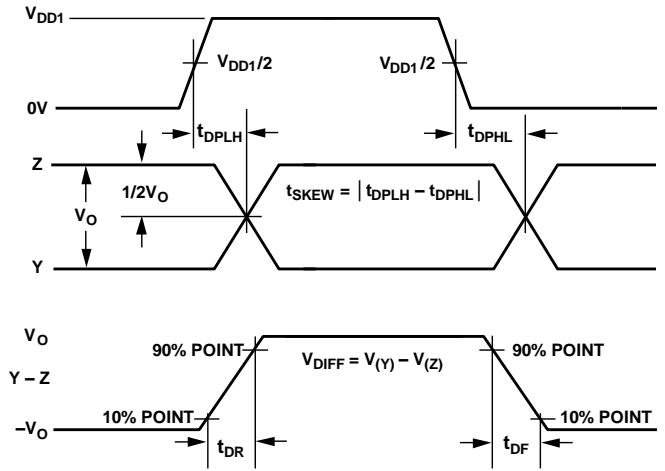


Figure 28. Driver Propagation Delay, Rise and Fall Timing

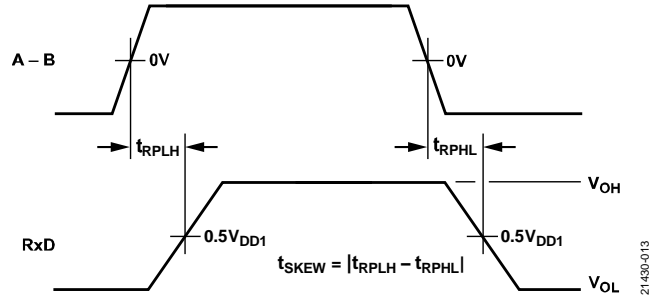


Figure 29. Receiver Propagation Delay

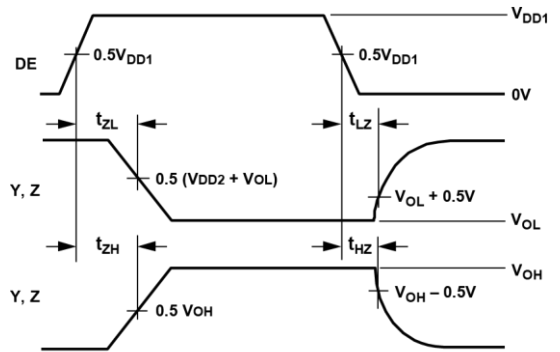


Figure 30. Driver Enable or Disable Timing

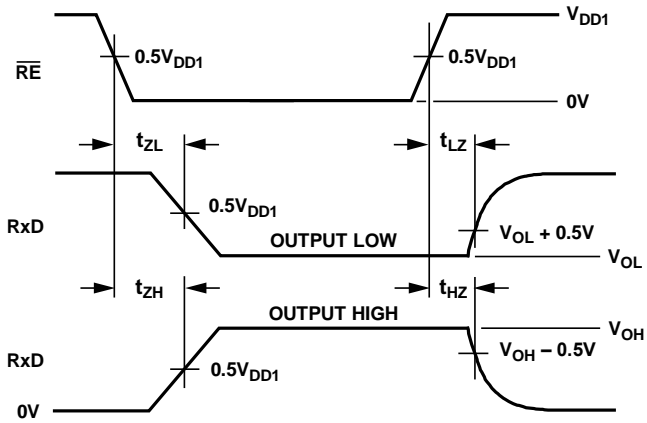


Figure 31. Receiver Enable or Disable Timing

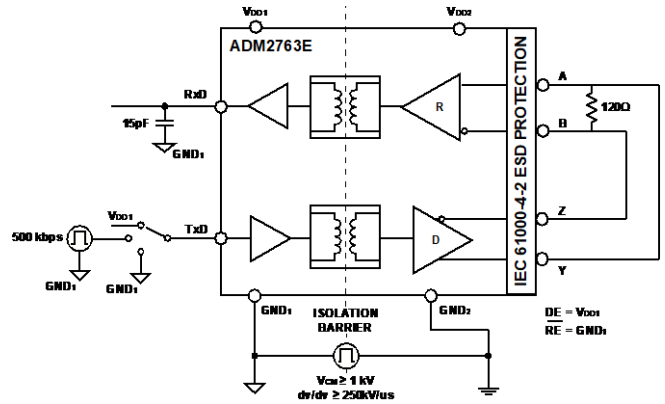


Figure 33. CMTI Test Diagram

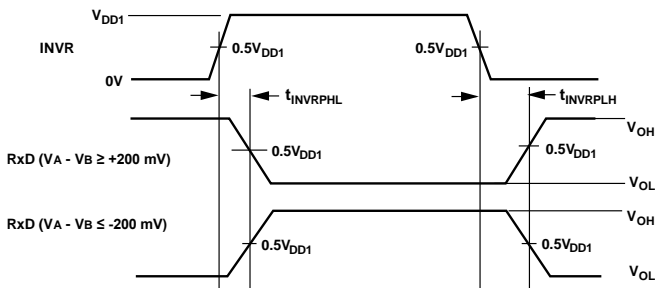


Figure 32. Receiver Cable Invert Timing Specification Measurement

## THEORY OF OPERATION

### ROBUST LOW POWER DIGITAL ISOLATOR

The ADM2763E features a low power, digital isolator block to galvanically isolate the primary and secondary sides of the device. The use of coplanar transformer coils with an on/off keying modulation scheme allows high data throughput across the isolation barrier while minimizing radiation emissions. This architecture provides a robust digital isolator with immunity to common-mode transients  $>250 \text{ kV}/\mu\text{s}$  across the full temperature and supply range of the device. The digital isolator circuitry features a flexible  $V_{DD1}$  power supply with an input voltage range of 1.7 V to 5.5 V.

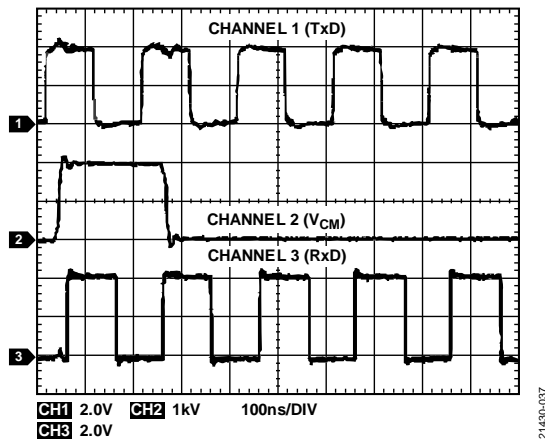


Figure 34. Switching Correctly in the Presence of  $>250 \text{ kV}/\mu\text{s}$  Common-Mode Transients

### HIGH DRIVER DIFFERENTIAL OUTPUT VOLTAGE

The ADM2763E features a proprietary transmitter architecture with a low driver output impedance that results in an increased differential output voltage. This architecture is useful when operating the device at lower data rates over long cable runs where the dc resistance of the transmission line dominates signal attenuation. In these applications, the increased differential voltage extends the reach of the device to longer cable lengths. When operated as a 5 V transceiver ( $V_{DD2} > 4.5 \text{ V}$ ), the ADM2763E meets or exceeds the Profibus requirement of a minimum 2.1 V differential output voltage.

### IEC61000-4-2 ESD PROTECTION

ESD is the sudden transfer of electrostatic charge between bodies at different potentials, which is either caused by near contact or induced by an electric field. ESD has the characteristics of a high current in a short time period. The primary purpose of the IEC61000-4-2 test is to determine system immunity to external ESD events outside the system during operation. IEC61000-4-2 describes testing using two coupling methods: contact discharge and air discharge. Contact discharge implies a direct contact between the discharge gun and the equipment under test (EUT). During air discharge testing, the charged electrode of the discharge gun is moved toward the EUT until a discharge occurs as an arc across the air gap. The discharge gun does not make direct contact

with the EUT during air discharge testing. Factors including humidity, temperature, barometric pressure, distance, and rate of approach to the EUT affect the results and repeatability of the air discharge test. This method is a better representation of an actual ESD event than the contact discharge method, but is not as repeatable. Therefore, contact discharge is the preferred test method. During testing, the data port is subjected to at least 10 positive and 10 negative single discharges. Test voltage selection depends on the system end environment. Figure 35 shows the 8 kV contact discharge current waveform, as described in the IEC61000-4-2 specification. Waveform parameters include rise times of  $<1 \text{ ns}$  and pulse widths of  $\sim 60 \text{ ns}$ .

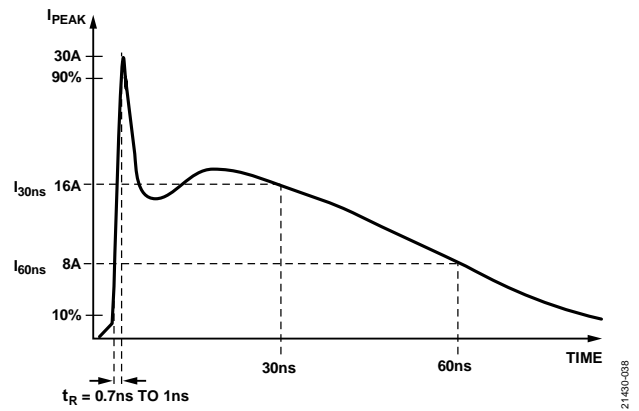


Figure 35. IEC61000-4-2 ESD Waveform (8 kV)

Figure 36 shows the 8 kV contact discharge current waveform from the IEC61000-4-2 standard compared to the human body model (HBM) ESD 8 kV waveform. Figure 36 shows that the two standards specify a different waveform shape and peak current ( $I_{PEAK}$ ). The  $I_{PEAK}$  associated with an IEC61000-4-2 8 kV pulse is 30 A, while the corresponding  $I_{PEAK}$  for HBM ESD is more than five times less at 5.33 A. The other key difference between the two standards is the rise time of the initial voltage spike. The IEC61000-4-2 ESD waveform has a faster rise time of 1 ns compared to the 10 ns associated with the HBM ESD waveform. The amount of power associated with an IEC ESD waveform is greater than that of an HBM ESD waveform. The HBM ESD standard requires the EUT to be subjected to three positive and three negative discharges, while the IEC ESD standard requires the EUT to be subjected to 10 positive and 10 negative discharge tests.

The ADM2763E is rated to  $\geq \pm 12 \text{ kV}$  contact ESD protection and  $\geq \pm 15 \text{ kV}$  air ESD protection between the RS-485 bus pins (A, B, Y, and Z) and the  $GND_2$  pin according to the IEC61000-4-2 standard. The isolation barrier provides  $\pm 8 \text{ kV}$  contact protection between the bus pins and the  $GND_1$  pin. This device with IEC61000-4-2 ESD ratings is better suited for operation in harsh environments when compared to other RS-485 transceivers that state varying levels of HBM ESD protection.

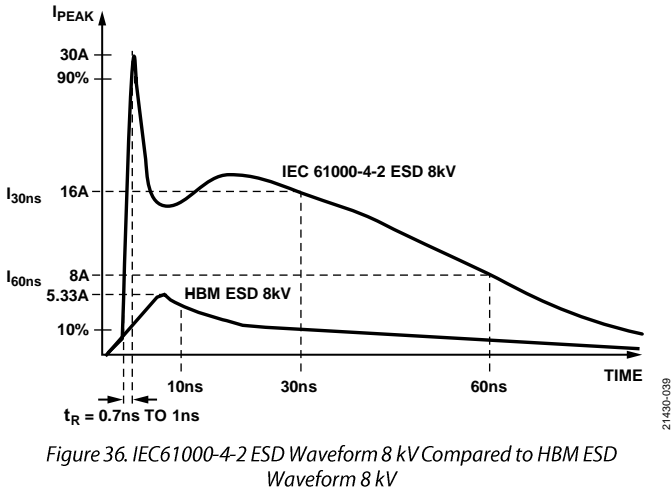


Table 13. Receiving Truth Table

Supply Status		Inputs			Outputs
V <sub>DD1</sub>	V <sub>DD2</sub>	A – B	INVR	$\overline{\text{RE}}$	RxD
On	On	$\geq -0.03 \text{ V}$	L	L	H
On	On	$\leq 0.03 \text{ V}$	H	L	H
On	On	$\leq -0.2 \text{ V}$	L	L	L
On	On	$\geq 0.2 \text{ V}$	H	L	L
On	On	$0.2 \text{ V} < \text{A} - \text{B} < -0.03 \text{ V}$	L	L	I
On	On	$0.03 \text{ V} < \text{A} - \text{B} < 0.2 \text{ V}$	H	L	I
On	On	Inputs open or shorted	L	L	H
On	On	Inputs open or shorted	H	L	H
On	On	X	X	H	Z
On	Off	X	X	H	Z
On	Off	X	X	L	I
Off	Off	X	X	H	I
Off	On	X	X	X	I

TRUTH TABLES

Table 12 and Table 13 use the abbreviations shown in Table 11. V<sub>DD1</sub> supplies the DE, TxD,  $\overline{\text{RE}}$ , RxD and INVR pins only.

Table 11. Truth Table Abbreviations

Letter	Description
H	High level
I	Indeterminate
L	Low level
X	Any state
Z	High impedance (off)
NC	Not connected

Table 12. Transmitting Truth Table

Supply Status		Outputs			
V <sub>DD1</sub>	V <sub>DD2</sub>	DE	TxD	Y	Z
On	On	H	H	H	L
On	On	H	H	L	H
On	On	H	L	L	H
On	On	H	L	H	L
On	On	L	X	Z	Z
Off	On	X	X	Z	Z
X	Off	X	X	Z	Z

RECEIVER FAIL-SAFE

The ADM2763E guarantees a logic high receiver output when the receiver inputs are shorted, open, or connected to a terminated transmission line with all drivers disabled. To achieve a fail-safe logic high output when the receiver inversion feature is disabled (INVR = 0 V), the receiver input threshold is set between -30 mV and -200 mV. If  $\text{A} - \text{B} \geq -30 \text{ mV}$ , the RxD output is logic high. If  $\text{A} - \text{B} \leq -200 \text{ mV}$ , the RxD output is logic low. To preserve the fail-safe feature when the receiver inversion feature is enabled on the ADM2463E (INVR = V<sub>DD1</sub>), the inverted receiver input threshold is set between 30 mV and 200 mV. In the case of a terminated bus with all transmitters disabled, the termination resistor pulls the receiver differential input voltage to 0 V, which results in a logic high RxD output with a 30 mV minimum noise margin. This feature eliminates the need for the external biasing components usually required to implement fail-safe.

These features are fully compatible with external fail-safe biasing configurations and can be used in applications with legacy devices that lack fail-safe support and in applications where additional noise margin is desired. See the [AN-960 Application Note, RS-485/RS-422 Circuit Implementation Guide](#), for details on external fail-safe biasing.



### RECEIVER CABLE INVERSION

The ADM2763E features receiver cable inversion functionality to correct for errors during installation. This adjustment can be implemented in the software on the controller driving the RS-485 transceiver to avoid additional installation costs to fix wiring errors. The ADM2763E full duplex transceiver features a receiver cable invert pin, INVR, that can be used to correct receiver functionality in cases where connections to the A and B pins are made incorrectly. When the receiver is inverted, the device maintains a Logic 1 receiver output with a 30 mV noise margin when inputs are shorted together or open circuit. Figure 37 shows the receiver input voltage thresholds in the inverted ( $INVR = V_{DD1}$ ) and noninverted ( $INVR = GND_1$ ) cases.

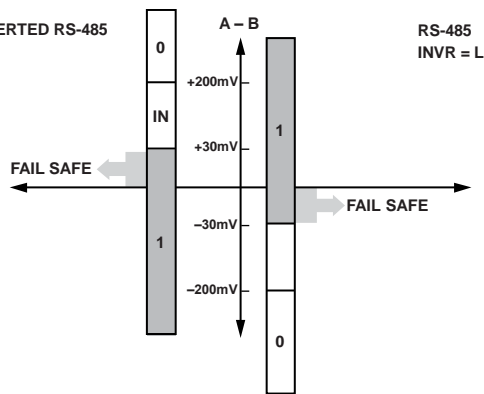


Figure 37. Noninverted RS-485 and Phase Inverted RS-485 Comparison

21430-040

### HOT SWAP INPUTS

When a circuit board is inserted into a powered (or hot) backplane, parasitic coupling from supply and ground rails to digital inputs can occur. The ADM2763E contains circuitry to ensure that the RS-485 driver outputs remain in a high impedance state during power-up, and then default to the correct states. For example, when  $V_{DD1}$  and  $V_{DD2}$  power up at the same time and the  $\overline{RE}$  pin is pulled low with the  $\overline{DE}$  and  $TxD$  pins pulled high, the A and B outputs remain in high impedance until the outputs settle at an expected default high for the A pin and expected default low for the B pin.

### 192 TRANSCEIVERS ON THE BUS

The standard RS-485 receiver input impedance is 12 k $\Omega$  (1 unit load) and the standard driver can drive up to 32 unit loads. The ADM2763E transceiver has a 1/6 unit load receiver input impedance (equivalent to 72 k $\Omega$ ) that allows up to 192 transceivers to be connected in parallel on one communication line. Any combination of these devices and other RS-485 transceivers with a total of 32 unit loads or fewer can be connected to the line.

### DRIVER OUTPUT PROTECTION

The ADM2763E has two methods to prevent excessive output current and power dissipation caused by faults or by bus contention. Current-limit protection on the output stage provides immediate protection against short circuits over the entire common-mode voltage range. In addition, a thermal shutdown circuit forces the driver outputs into a high impedance state if the die temperature rises excessively. This circuitry disables the driver outputs when a die temperature of 150°C is reached. As the device cools, the driver is reenabled at a temperature of 140°C.

## APPLICATIONS INFORMATION

### PCB LAYOUT AND ELECTROMAGNETIC INTERFERENCE (EMI)

The ADM2763E use a low power, on/off keying encoding scheme for robust communication with minimal radiated emissions. This device can meet EN55032 and CISPR 32 Class B requirements with margin on a standard 2-layer PCB, without the need for complex and area intensive layout techniques.

### MAXIMUM DATA RATE VS. AMBIENT TEMPERATURE

Under a large current load, power dissipation within the transceiver can limit the maximum ambient temperature achievable while retaining a silicon junction temperature below 150 °C. This internal power dissipation is related to application conditions such as supply voltage configuration, switching frequency, effective load on the RS-485 bus, and the amount of time the transceiver is in transmit mode. Thermal performance also depends on the PCB design and thermal characteristics of a system.

For high temperature applications above 85°C with a fully loaded RS-485 bus (equivalent to 54 Ω bus resistance) operating with a  $V_{DD2}$  supply of 5 V ±10%, limiting the transmitter data rate to 300 kbps is recommended. The thermal resistance ( $\theta_{JA}$ ) of the package can be used in conjunction with the typical performance curves for the  $V_{DD2}$  supply current to calculate the maximum data rate for a given ambient temperature.

### ISOLATED PROFIBUS SOLUTION

The ADM2763E has a driver that meets the requirements of an isolated Profibus node. When operating the ADM2763E as a Profibus transceiver, ensure that the  $V_{DD2}$  power supply is a minimum of 4.5 V. The ADM2763E is acceptable for use in Profibus applications as a result of the following characteristics:

- The output driver meets or exceeds the Profibus differential output requirements. To ensure that the transmitter differential output does not exceed 7 V p-p over all conditions, place 10 Ω resistors in series with the A and B transmitter outputs.
- Low bus pin capacitance of 28 pF.
- Class I (no loss of data) immunity to IEC61000-4-4 electrical fast transients (EFTs) up to ±1 kV with respect to the  $GND_2$  pin can be achieved using a Profibus shielded cable. IEC 61000-4-4 Class I to up ±3 kV can be achieved with the addition of a 470 pF capacitor connected between the  $GND_1$  pin and the RxD output pin.

### EMC, EFT, SURGE

In applications where additional levels of protection against IEC61000-4-5 EFT or IEC61000-4-4 surge events are required, external protection circuits can be added to enhance the EMC robustness of the device. See Figure 38 for a recommended EMC protection circuit that uses a series of SM712 transient voltage

suppressors (TVS) and 10 Ω pulse proof resistors to achieve Level 2 IEC61000-4-5 surge protection and an excess of Level 4 IEC61000-4-2 ESD and IEC61000-4-4 EFT protection. Table 14 and Table 15 list the protection levels and recommended protection components for this circuit.

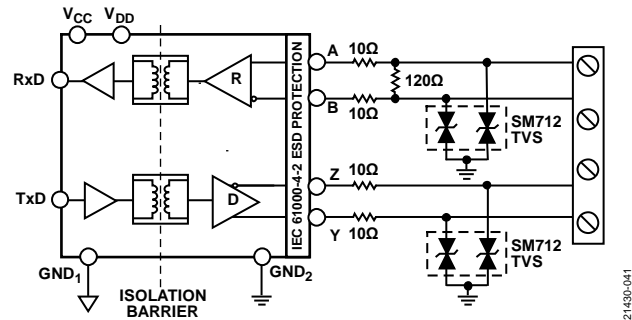


Figure 38. Isolated RS-485 Solution with ESD, EFT, and Surge Protection

Table 14. Recommended Components for ESD, EFT, and Surge Protection Solution

Recommended Components	Part Number
TVS	CDSOT23-SM712
10 Ω Pulse Proof Resistors	CRCW060310R0FKEAHP

Table 15. Protection Levels with Recommend Circuit

EMC Standard	Protection Level (kV)
ESD – Contact (IEC 61000-4-2)	≥±30 (exceeds Level 4)
ESD – Air (IEC 61000-4-2)	≥±30 (exceeds Level 4)
EFT (IEC 61000-4-4)	≥±4 (exceeds Level 4)
Surge (IEC 61000-4-5)	≥±1 (Level 2)

### INSULATION LIFETIME

All insulation structures eventually break down when subjected to voltage stress over a sufficiently long period of time. The rate of insulation degradation depends on the characteristics of the voltage waveform applied across the insulation and on the materials and material interfaces.

The two types of insulation degradation of primary interest are breakdown along surfaces exposed to the air and insulation wear out. Surface breakdown is the phenomenon of surface tracking and is the primary determinant of surface creepage requirements in system level standards. Insulation wear out is the phenomenon where charge injection or displacement currents inside the insulation material cause long-term insulation degradation.

#### Surface Tracking

Surface tracking is addressed in electrical safety standards by setting a minimum surface creepage based on the working voltage, the environmental conditions, and the properties of the insulation material. Safety agencies perform characterization testing on the surface insulation of components to allow the components to be categorized in different material groups. Lower material group ratings are more resistant to surface tracking and can provide adequate lifetime with smaller

creepage. The minimum creepage for a given working voltage and material group is in each system level standard and is based on the total rms voltage across the isolation, pollution degree, and material group. See Table 4 for the material group and creepage information for the ADM2763E isolated RS-485 transceivers.

**Insulation Wear Out**

The lifetime of insulation caused by wear out is determined by the insulation thickness, the material properties, and the voltage stress applied across the insulation. Ensure that the product lifetime is adequate at the application working voltage. The working voltage supported by an isolator for wear out may not be the same as the working voltage supported for tracking. The working voltage applicable to tracking is specified in most standards.

Testing and modeling show that the primary driver of long-term degradation is displacement current in the polyimide insulation, which causes incremental damage. The stress on the insulation can be divided into broad categories such as dc stress and ac component, time varying voltage stress. DC stress causes little wear out because there is no displacement current. AC component, time varying voltage stress causes wear out.

The ratings in certification documents are typically based on 60 Hz sinusoidal stress to reflect isolation from the line voltage. However, many practical applications have combinations of 60 Hz ac and dc across the barrier, as shown in Equation 1. Because only the ac portion of the stress causes wear out, the equation can be rearranged to solve for the ac rms voltage, as shown in Equation 2. For insulation wear out with the polyimide materials used in these products, the ac rms voltage determines the product lifetime.

$$V_{RMS} = \sqrt{V_{AC\ RMS}^2 + V_{DC}^2} \tag{1}$$

or

$$V_{AC\ RMS} = \sqrt{V_{RMS}^2 - V_{DC}^2} \tag{2}$$

where:

$V_{RMS}$  is the total rms working voltage.

$V_{AC\ RMS}$  is the time varying portion of the working voltage.

$V_{DC}$  is the dc offset of the working voltage.

**Calculation and Use of Parameters Example**

The following example frequently arises in power conversion applications. Assume that the line voltage on one side of the isolation is 240 V ac rms and a 400 V dc bus voltage is present on the other side of the isolation barrier. The isolator material is polyimide. To establish the critical voltages in determining the creepage, clearance, and lifetime of a device, see Figure 39, Equation 3, and Equation 4, where  $V_{PEAK}$  is the peak voltage.

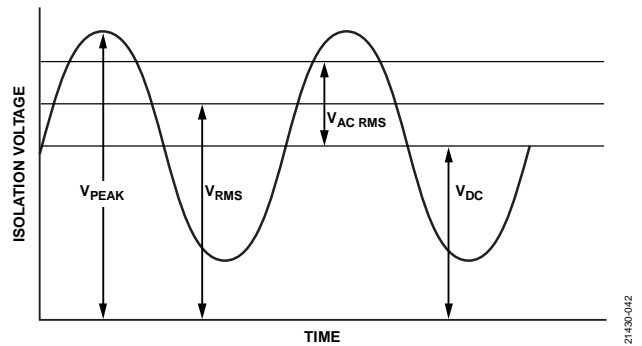


Figure 39. Critical Voltage Example

For this example, the  $V_{RMS}$  from Equation 1 is calculated as follows:

$$V_{RMS} = \sqrt{240^2 + 400^2} = 466\text{ V} \tag{3}$$

This  $V_{RMS}$  value is the working voltage used together with the material group and pollution degree when looking up the creepage required by a system standard.

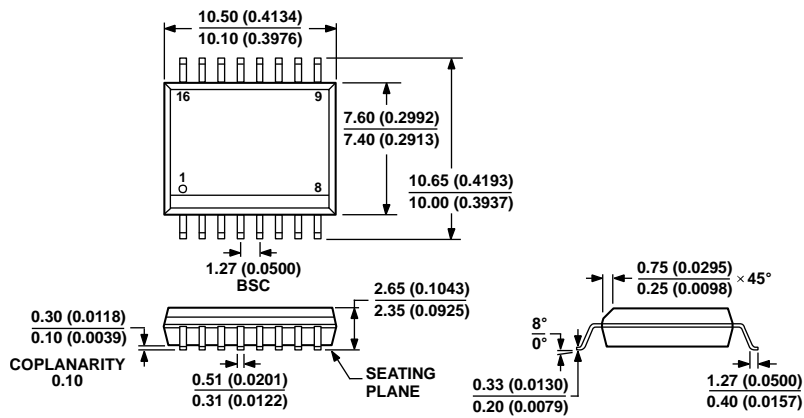
To determine if the lifetime is adequate, obtain the  $V_{AC\ RMS}$ . To calculate the  $V_{AC\ RMS}$  for this example, use Equation 2 as follows:

$$V_{AC\ RMS} = \sqrt{466^2 - 400^2} = 240\text{ V rms} \tag{4}$$

In this case, the  $V_{AC\ RMS}$  is the line voltage of 240 V rms. This calculation is more relevant when the waveform is not sinusoidal. The  $V_{AC\ RMS}$  value is compared to the limits for the working voltage in Table 9 for the expected lifetime (which is less than a 60 Hz sine wave) and is well within the limit for a 50-year service life.

Note that the dc working voltage limit is set by the creepage of the package, as specified in IEC60664-1. This dc value can differ for specific system level standards.

OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MS-013-AA  
 CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS  
 (IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR  
 REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 40. 16-Lead Standard Small Outline Package [SOIC\_W]  
 Wide Body (RW-16)  
 Dimensions shown in millimeters and (inches)

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